

62 mm C-Series module with CoolSiC™ Trench MOSFET and pre-applied thermal interface material

Features

- Electrical features
 - $V_{DSS} = 2000\text{ V}$
 - $I_{DN} = 400\text{ A} / I_{DRM} = 800\text{ A}$
 - Low switching losses
 - High current density
- Mechanical features
 - 4 kV AC 1 min insulation
 - Pre-applied thermal interface material



Potential applications

- UPS systems
- DC/DC converter
- High-frequency switching application
- Solar applications

Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

Description

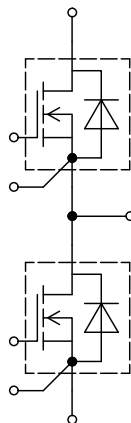


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1 Package

Table 1 Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, $f = 50 \text{ Hz}$, $t = 1 \text{ min}$	4.0	kV
Material of module baseplate			Cu	
Internal isolation		basic insulation (class 1, IEC 61140)	Al_2O_3	
Creepage distance	d_{Creep}	terminal to heatsink	29.0	mm
Creepage distance	d_{Creep}	terminal to terminal	23.0	mm
Clearance	d_{Clear}	terminal to heatsink	23.0	mm
Clearance	d_{Clear}	terminal to terminal	11.0	mm
Comparative tracking index	CTI		> 400	
Relative thermal index (electrical)	RTI	housing	140	°C

Table 2 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Stray inductance module	L_{sCE}			20		nH
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	$T_C = 25 \text{ °C}$, per switch		0.465		mΩ
Storage temperature	T_{stg}		-40		125	°C
Maximum baseplate operation temperature	T_{BPmax}				125	°C
Mounting torque for module mounting	M	- Mounting according to valid application note	M6, Screw	3	6	Nm
Terminal connection torque	M	- Mounting according to valid application note	M6, Screw	2.5	5	Nm
Weight	G			340		g

Note: Storage and shipment of modules with TIM => see AN2012-07

2 MOSFET, T1 / T2

Table 3 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Drain-source voltage	V_{DSS}	$T_{vj} = 25 \text{ °C}$	2000	V
Implemented drain current	I_{DN}		400	A

(table continues...)

Table 3 (continued) Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Continuous DC drain current	I_{DDC}	$T_{\text{vj}} = 175\text{ °C}$, $V_{\text{GS}} = 18\text{ V}$ $T_{\text{H}} = 25\text{ °C}$	325	A
Repetitive peak drain current	I_{DRM}	verified by design, t_{p} limited by T_{vjmax}	800	A
Gate-source voltage, max. transient voltage	V_{GS}	$D < 0.01$	-10/23	V
Gate-source voltage, max. static voltage	V_{GS}		-7/20	V

Table 4 Recommended values

Parameter	Symbol	Note or test condition	Values	Unit
On-state gate voltage	$V_{\text{GS(on)}}$		18	V
Off-state gate voltage	$V_{\text{GS(off)}}$		-3	V

Table 5 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Drain-source on-resistance	$R_{\text{DS(on)}}$	$I_{\text{D}} = 400\text{ A}$	$V_{\text{GS}} = 18\text{ V}$, $T_{\text{vj}} = 25\text{ °C}$	2.6	4	mΩ
			$V_{\text{GS}} = 18\text{ V}$, $T_{\text{vj}} = 125\text{ °C}$	5.5		
			$V_{\text{GS}} = 18\text{ V}$, $T_{\text{vj}} = 175\text{ °C}$	7.8		
Gate threshold voltage	$V_{\text{GS(th)}}$	$I_{\text{D}} = 224\text{ mA}$, $V_{\text{DS}} = V_{\text{GS}}$, $T_{\text{vj}} = 25\text{ °C}$, (tested after 1ms pulse at $V_{\text{GS}} = +20\text{ V}$)	3.45	4.3	5.15	V
Total gate charge	Q_{G}	$V_{\text{DD}} = 1200\text{ V}$, $V_{\text{GS}} = -3/18\text{ V}$		1.56		μC
Internal gate resistor	R_{Gint}	$T_{\text{vj}} = 25\text{ °C}$		0.9		Ω
Input capacitance	C_{ISS}	$f = 100\text{ kHz}$, $V_{\text{DS}} = 1200\text{ V}$, $V_{\text{GS}} = 0\text{ V}$ $T_{\text{vj}} = 25\text{ °C}$		48.2		nF
Output capacitance	C_{OSS}	$f = 100\text{ kHz}$, $V_{\text{DS}} = 1200\text{ V}$, $V_{\text{GS}} = 0\text{ V}$ $T_{\text{vj}} = 25\text{ °C}$		1.13		nF
Reverse transfer capacitance	C_{rSS}	$f = 100\text{ kHz}$, $V_{\text{DS}} = 1200\text{ V}$, $V_{\text{GS}} = 0\text{ V}$ $T_{\text{vj}} = 25\text{ °C}$		0.08		nF
C_{OSS} stored energy	E_{OSS}	$V_{\text{DS}} = 1200\text{ V}$, $V_{\text{GS}} = -3/18\text{ V}$, $T_{\text{vj}} = 25\text{ °C}$		2030		μJ
Drain-source leakage current	I_{DSS}	$V_{\text{DS}} = 2000\text{ V}$, $V_{\text{GS}} = -3\text{ V}$ $T_{\text{vj}} = 25\text{ °C}$		0.08	660	μA
Gate-source leakage current	I_{GSS}	$V_{\text{DS}} = 0\text{ V}$, $T_{\text{vj}} = 25\text{ °C}$ $V_{\text{GS}} = 20\text{ V}$			400	nA

(table continues...)

Table 5 (continued) **Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Turn-on delay time (inductive load)	$t_{d\ on}$	$I_D = 400\ A, R_{Gon} = 8.2\ \Omega, V_{DD} = 1200\ V, V_{GS} = -3/18\ V$	$T_{vj} = 25\ ^\circ C$	286		ns
			$T_{vj} = 125\ ^\circ C$	258		
			$T_{vj} = 175\ ^\circ C$	248		
Rise time (inductive load)	t_r	$I_D = 400\ A, R_{Gon} = 8.2\ \Omega, V_{DD} = 1200\ V, V_{GS} = -3/18\ V$	$T_{vj} = 25\ ^\circ C$	266		ns
			$T_{vj} = 125\ ^\circ C$	252		
			$T_{vj} = 175\ ^\circ C$	239		
Turn-off delay time (inductive load)	$t_{d\ off}$	$I_D = 400\ A, R_{Goff} = 2.2\ \Omega, V_{DD} = 1200\ V, V_{GS} = -3/18\ V$	$T_{vj} = 25\ ^\circ C$	226		ns
			$T_{vj} = 150\ ^\circ C$	244		
			$T_{vj} = 175\ ^\circ C$	255		
Fall time (inductive load)	t_f	$I_D = 400\ A, R_{Goff} = 2.2\ \Omega, V_{DD} = 1200\ V, V_{GS} = -3/18\ V$	$T_{vj} = 25\ ^\circ C$	57.5		ns
			$T_{vj} = 150\ ^\circ C$	57.7		
			$T_{vj} = 175\ ^\circ C$	60.5		
Turn-on energy loss per pulse	E_{on}	$I_D = 400\ A, V_{DD} = 1200\ V, L_\sigma = 25\ nH, V_{GS} = -3/18\ V, R_{Gon} = 8.2\ \Omega, di/dt = 3.2\ kA/\mu s (T_{vj} = 175\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$	75.3		mJ
			$T_{vj} = 125\ ^\circ C$	75.8		
			$T_{vj} = 175\ ^\circ C$	79.8		
Turn-off energy loss per pulse	E_{off}	$I_D = 400\ A, V_{DD} = 1200\ V, L_\sigma = 25\ nH, V_{GS} = -3/18\ V, R_{Goff} = 2.2\ \Omega, dv/dt = 15.9\ kV/\mu s (T_{vj} = 175\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$	24.3		mJ
			$T_{vj} = 125\ ^\circ C$	25.5		
			$T_{vj} = 175\ ^\circ C$	26.7		
Thermal resistance, junction to heat sink	R_{thJH}	per MOSFET, Valid with IFX pre-applied Thermal Interface Material			0.118	K/W
Temperature under switching conditions	$T_{vj\ op}$		-40		175	$^\circ C$

Note: The selection of positive and negative gate-source voltages impacts losses and the long-term behavior of the MOSFET and body diode. The design guidelines described in Application Notes AN 2018-09 and AN 2021-13 must be considered to ensure sound operation of the device over the planned lifetime.

$T_{vj,op} > 150^\circ C$ is allowed for operation at overload conditions for MOSFET and body diode. For detailed specifications, please refer to AN 2021-13.

3 Body diode (MOSFET, T1 / T2)

Table 6 **Maximum rated values**

Parameter	Symbol	Note or test condition	Values	Unit
DC body diode forward current	I_{SD}	$T_{vj} = 175\ ^\circ C, V_{GS} = -3\ V$ $T_H = 25\ ^\circ C$	235	A

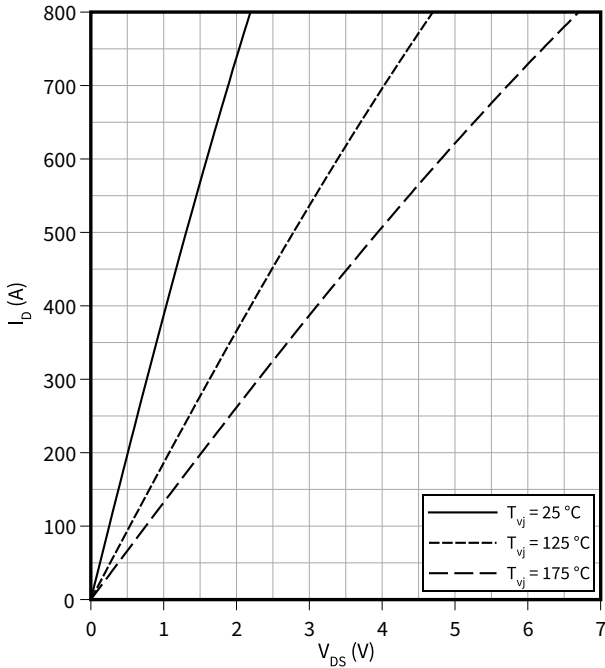
Table 7 **Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Forward voltage	V_{SD}	$I_{SD} = 400 \text{ A}, V_{GS} = -3 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$		4.6	6.15	V
			$T_{vj} = 125 \text{ }^\circ\text{C}$		4.15		
			$T_{vj} = 175 \text{ }^\circ\text{C}$		4		

4 Characteristics diagrams

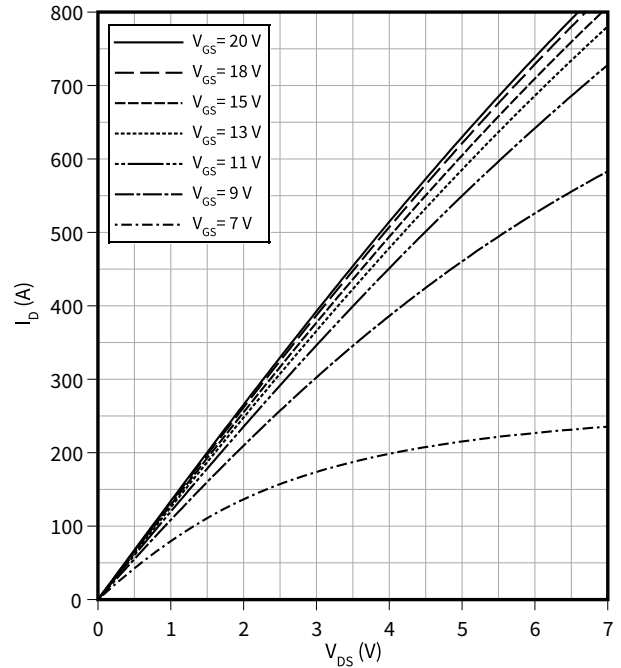
Output characteristic (typical), MOSFET, T1 / T2

$I_D = f(V_{DS})$
 $V_{GS} = 18\text{ V}$



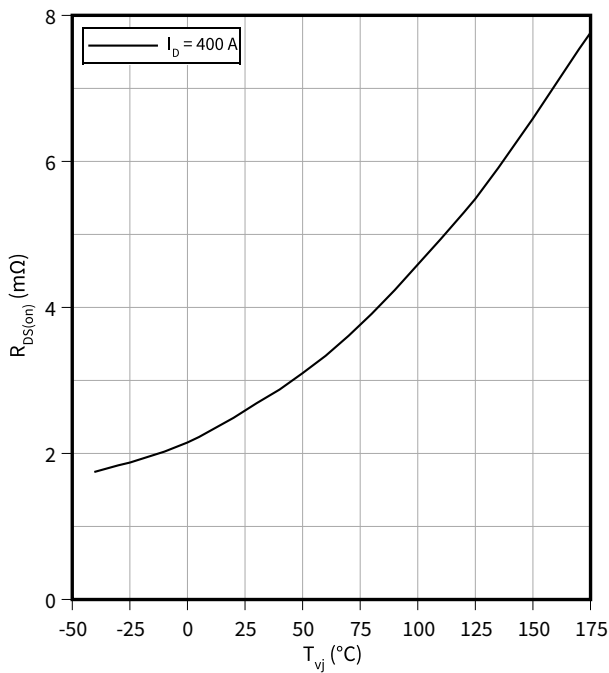
Output characteristic field (typical), MOSFET, T1 / T2

$I_D = f(V_{DS})$
 $T_{vj} = 175\text{ °C}$



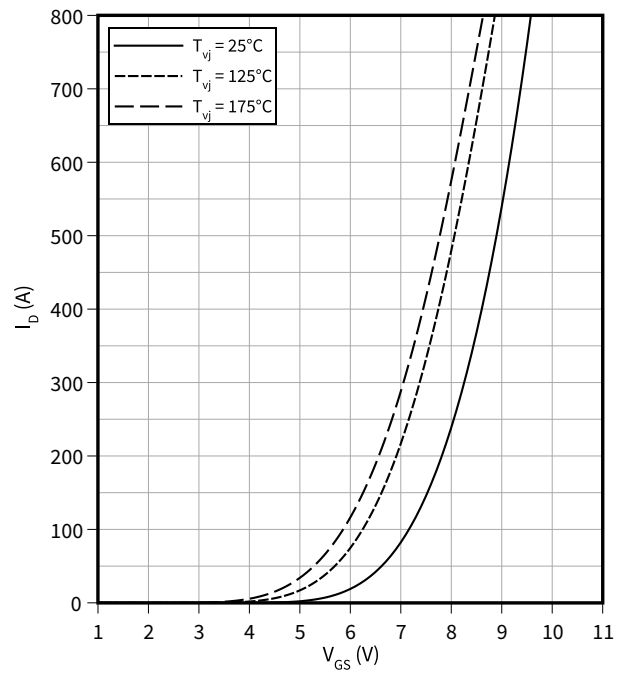
Drain source on-resistance (typical), MOSFET, T1 / T2

$R_{DS(on)} = f(T_{vj})$
 $V_{GS} = 18\text{ V}$



Transfer characteristic (typical), MOSFET, T1 / T2

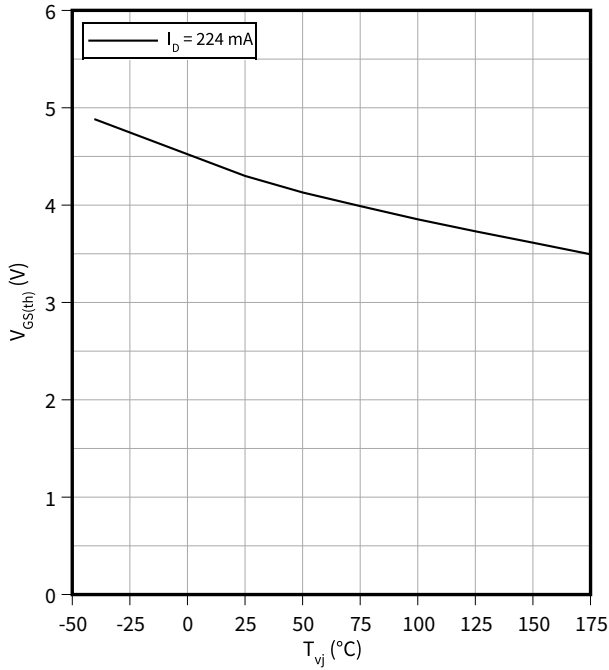
$I_D = f(V_{GS})$
 $V_{DS} = 20\text{ V}$



4 Characteristics diagrams

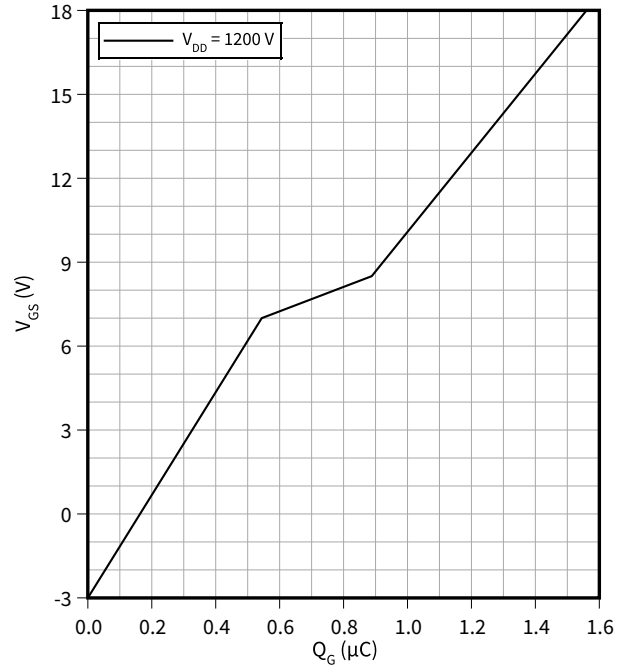
Gate-source threshold voltage (typical), MOSFET, T1 / T2

$V_{GS(th)} = f(T_{vj})$
 $V_{GS} = V_{DS}$



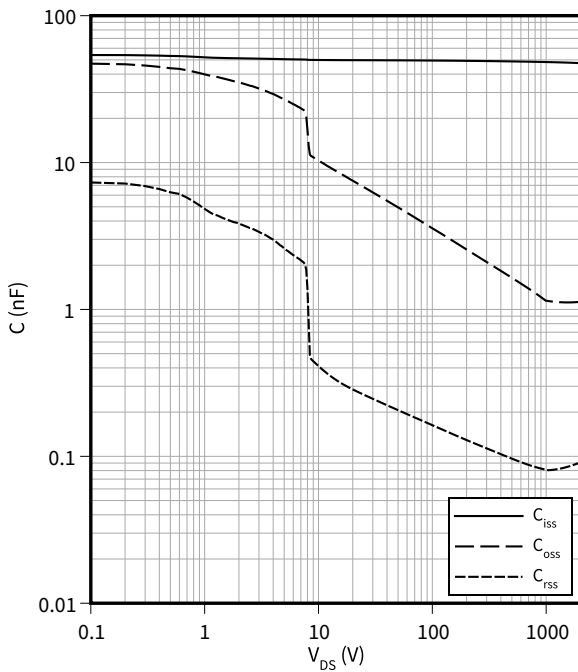
Gate charge characteristic (typical), MOSFET, T1 / T2

$V_{GS} = f(Q_G)$
 $I_D = 400 \text{ A}, T_{vj} = 25 \text{ °C}$



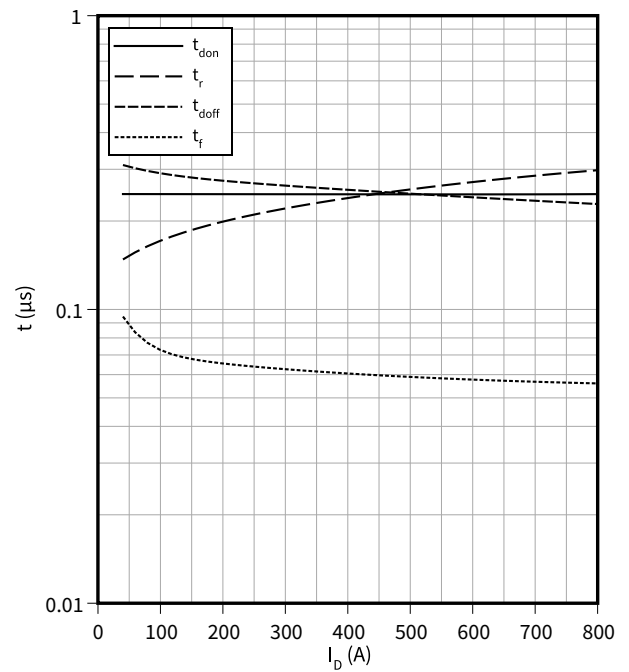
Capacity characteristic (typical), MOSFET, T1 / T2

$C = f(V_{DS})$
 $f = 100 \text{ kHz}, T_{vj} = 25 \text{ °C}, V_{GS} = -3 \text{ V}$



Switching times (typical), MOSFET, T1 / T2

$t = f(I_D)$
 $R_{Goff} = 2.2 \text{ } \Omega, R_{Gon} = 8.2 \text{ } \Omega, V_{DD} = 1200 \text{ V}, T_{vj} = 175 \text{ °C}, V_{GS} = -3/18 \text{ V}$

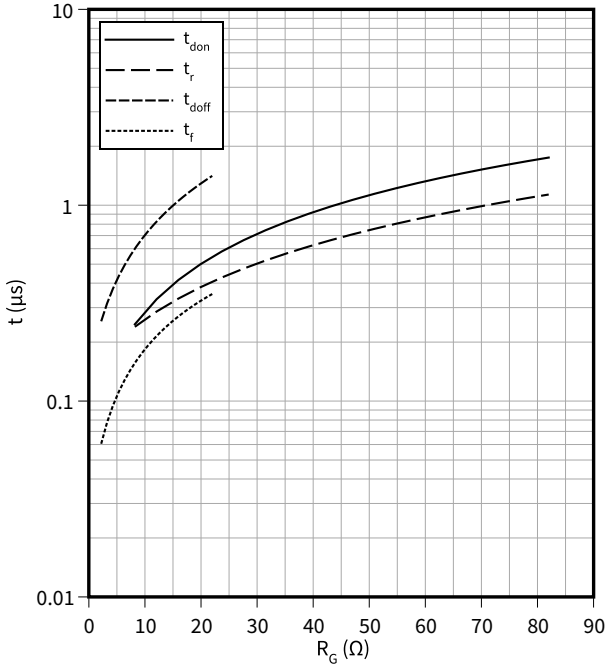


4 Characteristics diagrams

Switching times (typical), MOSFET, T1 / T2

$t = f(R_G)$

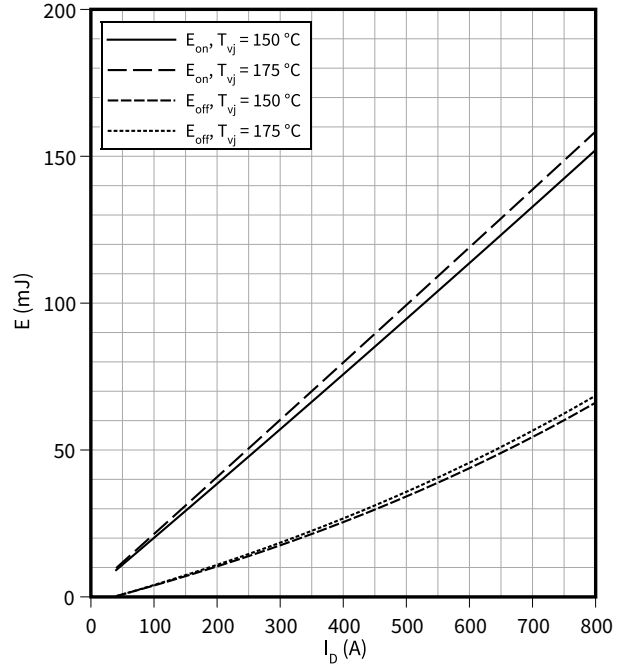
$V_{DD} = 1200\text{ V}$, $I_D = 400\text{ A}$, $T_{vj} = 175\text{ }^\circ\text{C}$, $V_{GS} = -3/18\text{ V}$



Switching losses (typical), MOSFET, T1 / T2

$E = f(I_D)$

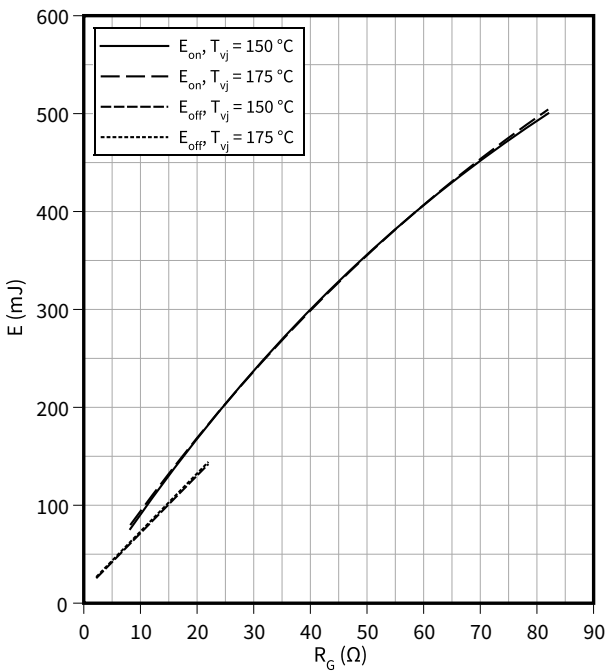
$R_{Goff} = 2.2\ \Omega$, $R_{Gon} = 8.2\ \Omega$, $V_{DD} = 1200\text{ V}$, $V_{GS} = -3/18\text{ V}$



Switching losses (typical), MOSFET, T1 / T2

$E = f(R_G)$

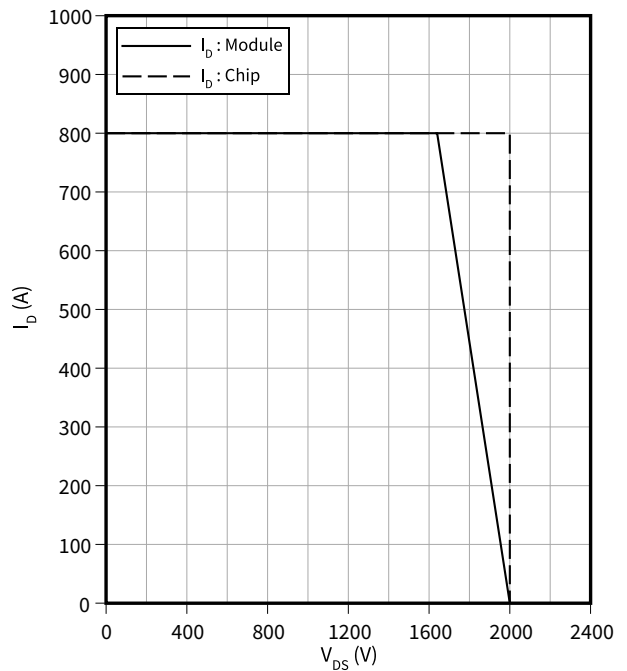
$V_{DD} = 1200\text{ V}$, $I_D = 400\text{ A}$, $V_{GS} = -3/18\text{ V}$



Reverse bias safe operating area (RBSOA), MOSFET, T1 / T2

$I_D = f(V_{DS})$

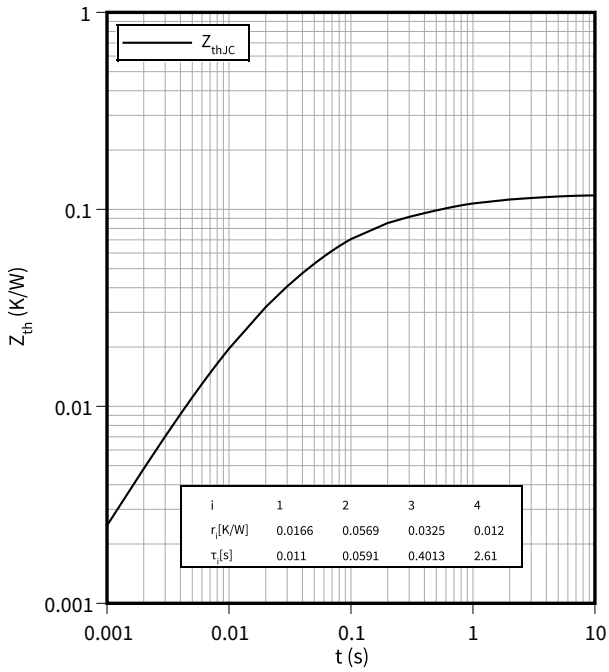
$R_{Goff} = 2.2\ \Omega$, $T_{vj} = 175\text{ }^\circ\text{C}$, $V_{GS} = -3/18\text{ V}$



4 Characteristics diagrams

Transient thermal impedance, MOSFET, T1 / T2

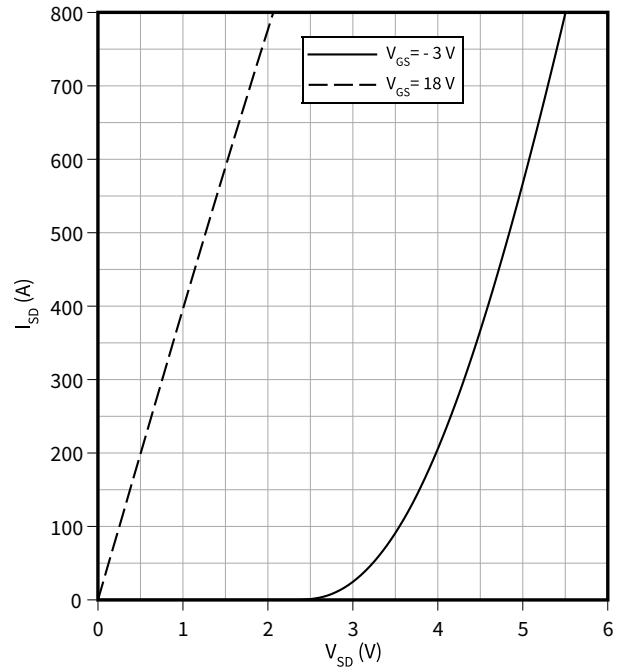
$Z_{th} = f(t)$



Forward characteristic body diode (typical), MOSFET, T1 / T2

$I_{SD} = f(V_{SD})$

$T_{vj} = 25\text{ }^\circ\text{C}$



5 Circuit diagram

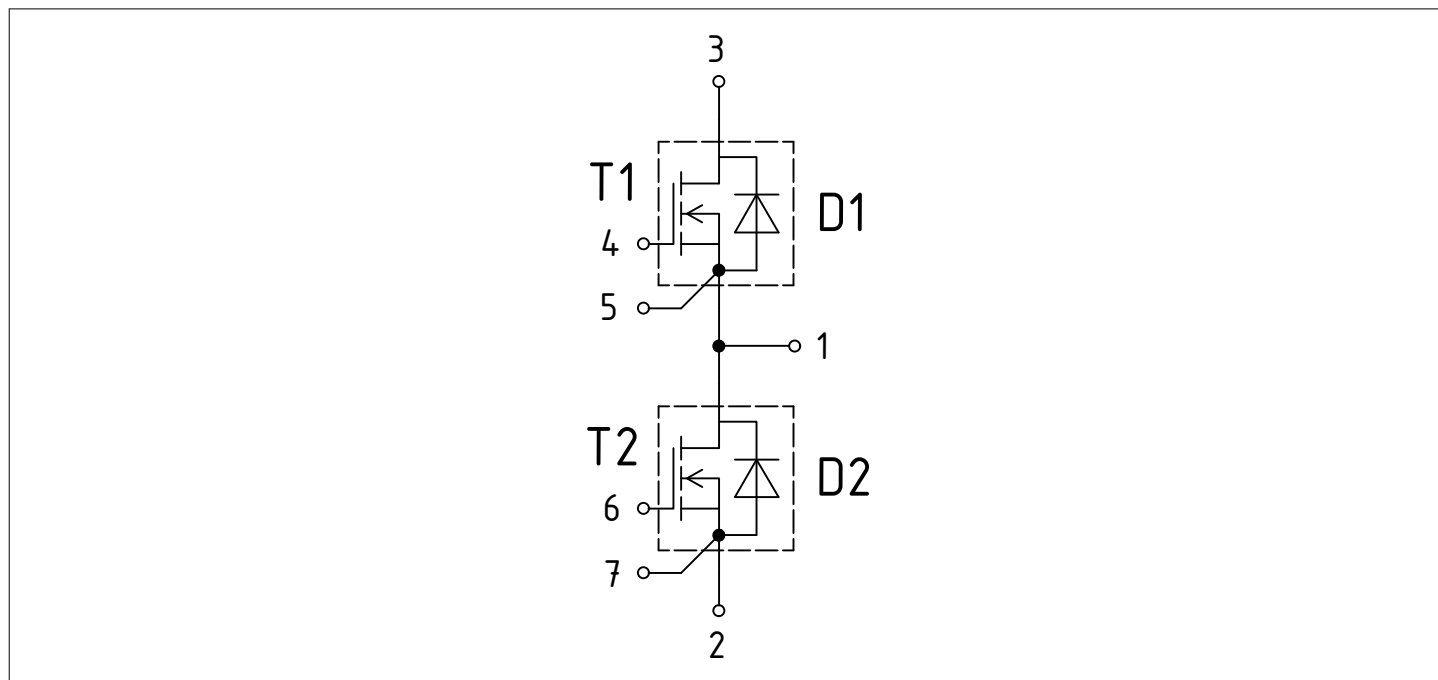


Figure 1

6 Package outlines

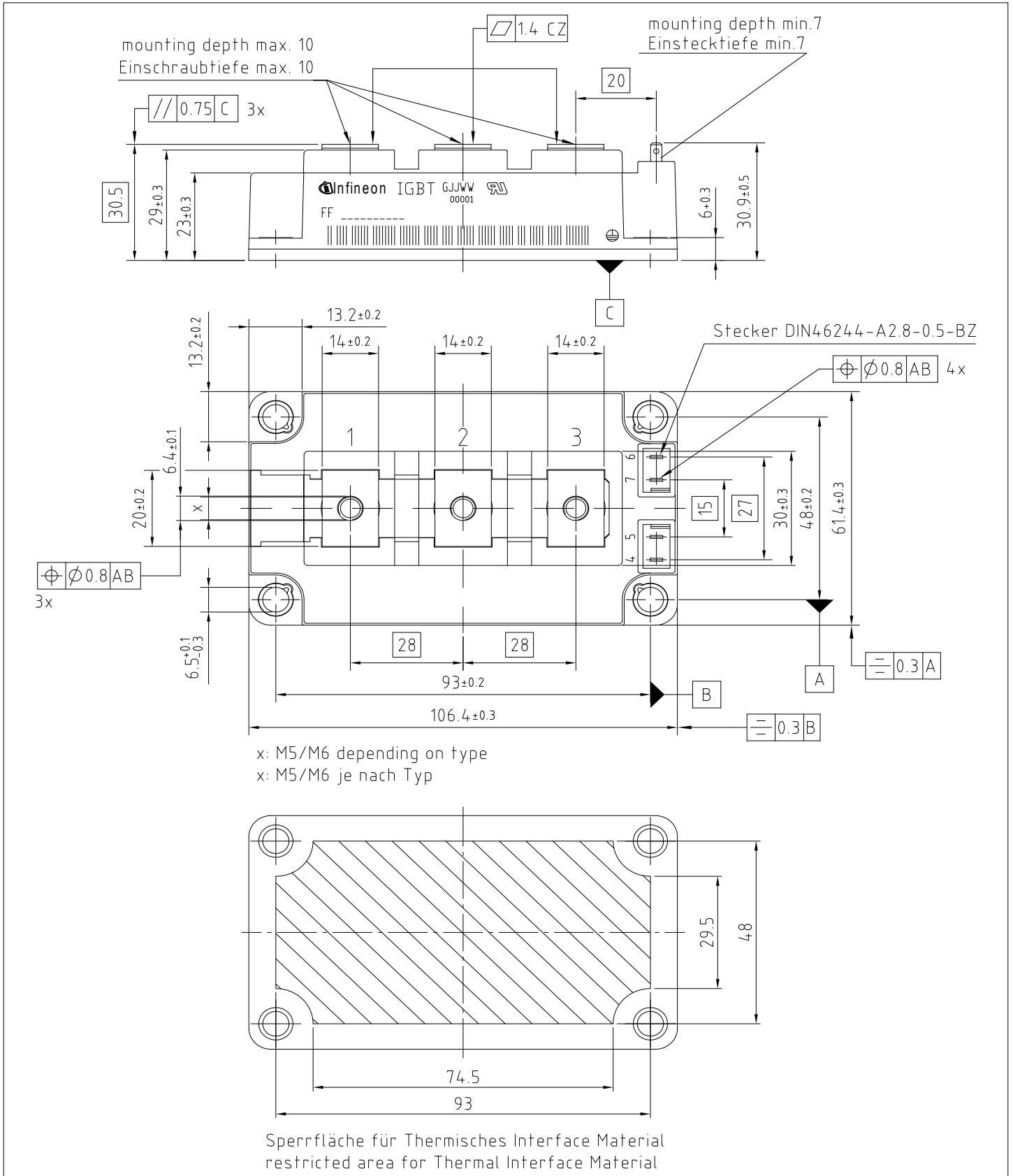


Figure 2

7 Module label code

Module label code			
Code format	Data Matrix	Barcode Code128	
Encoding	ASCII text	Code Set A	
Symbol size	16x16	23 digits	
Standard	IEC24720 and IEC16022	IEC8859-1	
Code content	<i>Content</i>	<i>Digit</i>	<i>Example</i>
	Module serial number	1 - 5	71549
	Module material number	6 - 11	142846
	Production order number	12 - 19	55054991
	Date code (production year)	20 - 21	15
	Date code (production week)	22 - 23	30
Example	 		
	71549142846550549911530		71549142846550549911530

Figure 3

Revision history

Document revision	Date of release	Description of changes
1.00	2023-05-05	Initial version

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